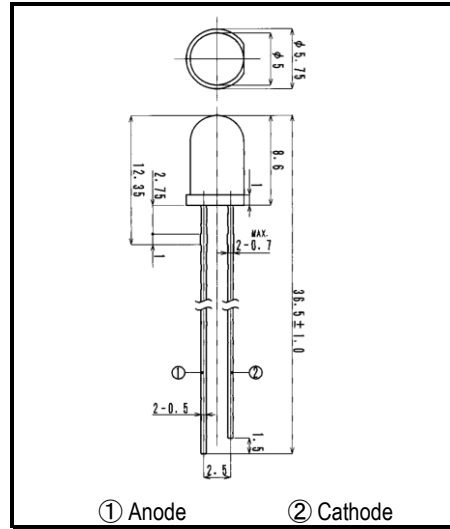
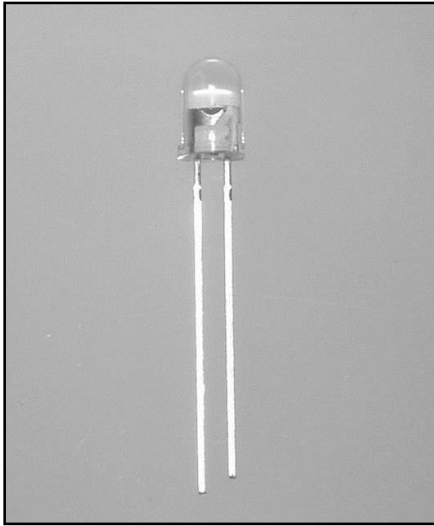


LSF946N1

Infrared Emitting Diode



FEATURES

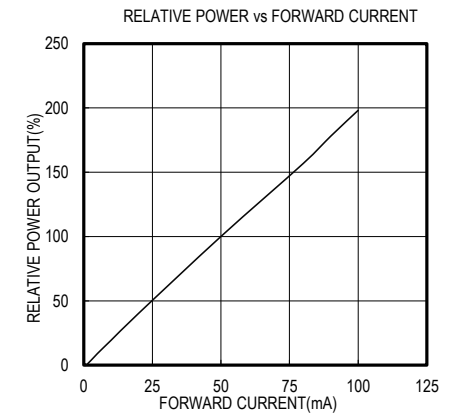
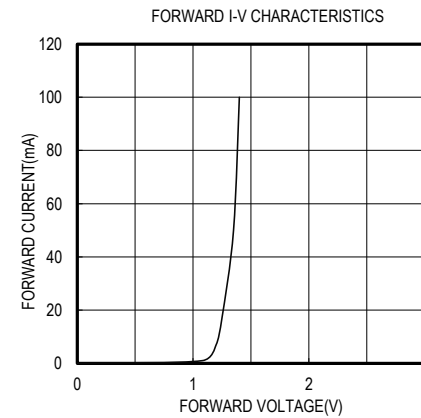
- High-output Power
- High Reliability

APPLICATIONS

- Optical Switches
- Optical sensors

2. ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25°C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=50mA		22.0		mW
Forward Voltage	VF	IF=50mA		1.30	1.9	V
Reverse Current	IR	VR=5V			100	μA
Peak Wavelength	λ _p	IF=50mA		950		nm
Spectral Line Half Width	Δλ	IF=50mA		40		nm
Half Intensity Beam Angle	θ	IF=50mA		±15		deg.

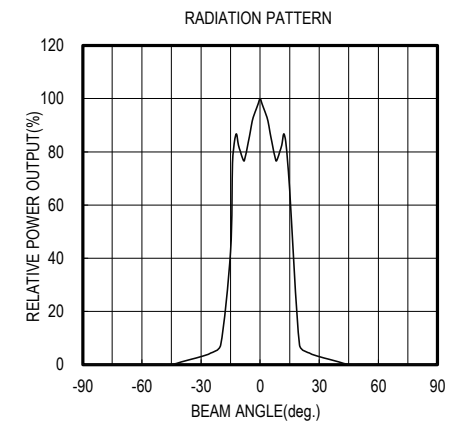
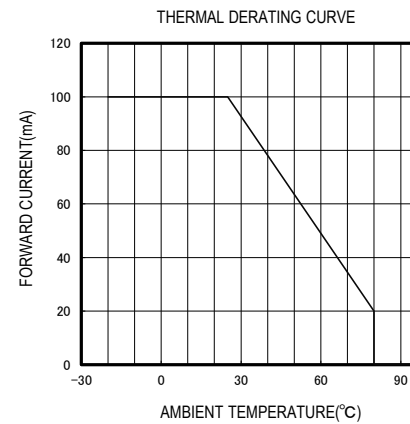
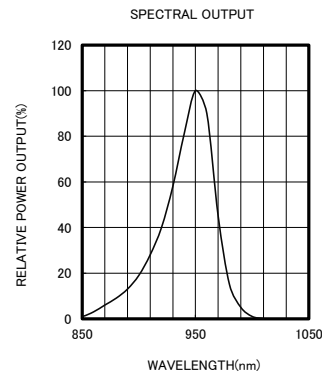


1. ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

ITEM	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	100	mA
Forward Current (Pulse)*1	IFP	1	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	190	mW
Operating Temp.	Topr	-20 TO 80	°C
Storage Temp.	Tstg	-30 TO 100	°C
Junction Temp.	Tj	100	°C
Lead Soldering Temp.*2	Tls	260	°C

*1: Tw=10μs, T=1ms

*2: Time 5 Sec max, Position: Up to 3mm from the body



OPTRANS

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